Lightning Surge Protection - SLVU2.8-4 Series

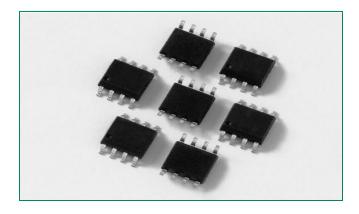


# SLVU2.8-4 Series 2.8V 40A TVS Array

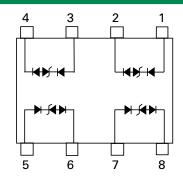




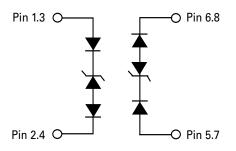




#### **Pinout**



#### **Functional Block Diagram**



### **Additional Information**







# **Description**

The SLVU2.8-4 was designed to protect low voltage, CMOS devices from ESD and lightning induced transients. There is a compensating diode in series with each low voltage TVS to present a low loading capacitance to the line being protected. These robust structures can safely absorb repetitive ESD strikes at  $\pm 30 \text{kV}$  (contact discharge) per IEC 61000-4-2 standard and each structure can safely dissipate up to 40A (IEC 61000-4-5 2nd edition,  $t_\text{p}=8/20 \mu\text{s})$  with very low clamping voltages.

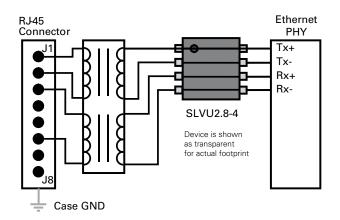
#### **Features**

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, IEC 61000-4-5 2nd edition, 40A (8/20µs)
- Low capacitance of 2pF per line
- Low leakage current of 1µA (MAX) at 2.8V
- SOIC-8 (JEDEC MO-012) pin configuration allows for simple flow-through layout
- RoHS Compliant and Lead Free
- Moisture Sensitivity Level (MSL-1)

#### **Applications**

- 10/100/1000 Ethernet
- WAN/LAN Equipment
- Switching Systems
- Desktops, Servers, and Notebooks
- Analog Inputs
- Base Stations

#### **Application Example**





# **Electrical Characteristics (T<sub>OP</sub> = 25°C)**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage V <sub>RWM</sub>		I <sub>R</sub> ≤1μA			2.8	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> =2μA	3.0			V
Snap Back Voltage	V <sub>SB</sub>	I <sub>T</sub> =50mA	2.8			V
Reverse Leakage Current	I <sub>LEAK</sub>	V <sub>R</sub> =2.8V (Each Line)			1	μΑ
Clamping Voltage <sup>1</sup>	V <sub>C</sub>	I <sub>pp</sub> =5A, t <sub>p</sub> =8/20μs (Each Line)		7.0	8.5	V
Clamping Voltage <sup>1</sup>	V <sub>C</sub>	I <sub>PP</sub> =24A, t <sub>P</sub> =8/20μs (Each Line)		13.9	15.0	V
ESD Withstand Voltage <sup>1</sup>	.,	IEC61000-4-2 (Contact)	±30			kV
	V <sub>ESD</sub>	IEC61000-4-2 (Air)	±30			kV
Dynamic Resistance	R <sub>DYN</sub>	(V <sub>C2</sub> - V <sub>C1</sub> ) / (I <sub>PP2</sub> - I <sub>PP1</sub> ) (Each Line)		0.4		Ω
Diode Capacitance <sup>1</sup>	C <sub>D</sub>	V <sub>R</sub> =0V, f=1MHz (Each Line)		2.0	2.5	pF

Note: 1Parameter is guaranteed by design and/or device characterization.

Absolute Maximum Ratings				
Parameter	Rating	Units		
Peak Pulse Power (t <sub>p</sub> =8/20µs)	600	W		
Peak Pulse Current (t <sub>P</sub> =8/20µs)	40	А		
Operating Temperature	–40 to 125	°C		
Storage Temperature	-55 to 150	°C		

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Figure 1: Capacitance vs. Reverse Voltage

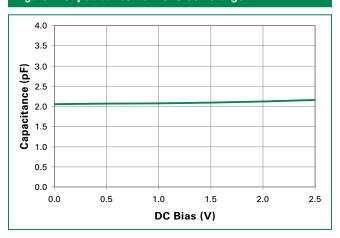


Figure 2: Clamping Voltage vs. Ipp

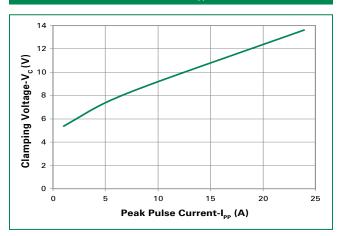
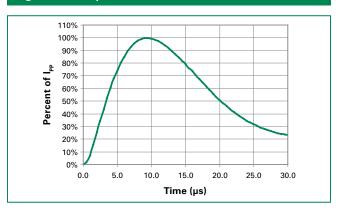


Figure 3: 8/20 µs Pulse Waveform





#### **Product Characteristics**

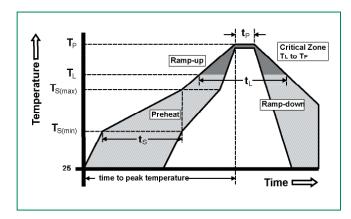
Lead Plating	MatteTin	
Lead Material	Copper Alloy	
Lead Coplanarity	0.0004 inches (0.102mm)	
Substitute Material	Silicon	
Body Material	V-0 per UL 94 Molded Epoxy	

- All dimensions are in millimeters
   Dimensions include solder plating.

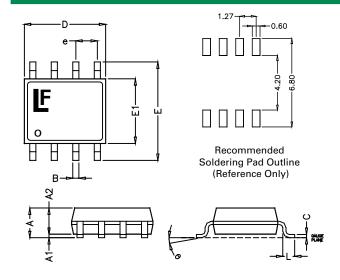
- Dimensions include solder plating.
   Dimensions are exclusive of mold flash & metal burr.
   All specifications comply to JEDEC SPEC MO-203 Issue A
   Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
   Package surface matte finish VDI 11-13.

# **Soldering Parameters**

Reflow Condition		Pb – Free assembly	
	-Temperature Min (T <sub>s(min)</sub> )	150°C	
Pre Heat	-Temperature Max (T <sub>s(max)</sub> )	200°C	
	-Time (min to max) (t <sub>s</sub> )	60 – 180 secs	
Average ramp up rate (Liquidus) Temp (T <sub>1</sub> ) to peak		5°C/second max	
T <sub>S(max)</sub> to T <sub>L</sub> - Ramp-up Rate		5°C/second max	
Reflow	-Temperature (T <sub>L</sub> ) (Liquidus)	217°C	
	-Temperature (t <sub>L</sub> )	60 – 150 seconds	
PeakTemperature (T <sub>P</sub> )		260+0/-5 °C	
Time within 5°C of actual peak Temperature (t <sub>p</sub> )		20 - 40 seconds	
Ramp-down Rate		5°C/second max	
Time 25°C to peakTemperature (T <sub>P</sub> )		8 minutes Max.	
Do not exceed		260°C	



# Package Dimensions — Mechanical Drawings and Recommended Solder Pad Outline



Package	SOIC-8					
Pins	8					
JEDEC	MS-012					
	Millin	netres	Inc	Inches		
	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
<b>A</b> 1	0.10	0.25	0.004	0.010		
A2	1.25	1.65	0.050	0.065		
В	0.31	0.51	0.012	0.020		
С	0.17	0.25	0.007	0.010		
D	4.80	5.00	0.189	0.197		
E	5.80	6.20	0.228	0.244		
E1	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050	BSC		
L	0.40	0.40 1.27 0.016 C		0.050		

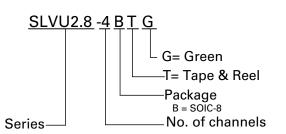
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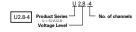
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### **Part Numbering System**



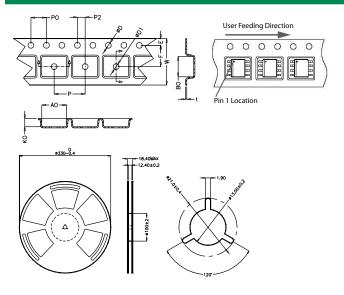
# **Part Marking System**



# **Ordering Information**

Part Number	Package	Marking	Min. Order Qty.
SLVU2.8-4BTG	SOIC-8	U2.8-4	2500

## **Embossed Carrier Tape & Reel Specification — SOIC Package**



0 1 1	Millimetres		Inches			
Symbol	Min	Max	Min	Max		
E	1.65	1.85	0.065	0.073		
F	5.4	5.6	0.213	0.22		
P2	1.9	2.1	0.075	0.083		
D	1.5	1.6	0.059	0.063		
D1	1.50	Min	0.059	9 Min		
P0	3.9	4.1	0.154	0.161		
10P0	40.0 ± 0.20		1.574 ±	± 0.008		
W	11.9	12.1	0.468	0.476		
P	7.9	8.1	0.311	0.319		
A0	6.3	6.5	0.248	0.256		
В0	5.1	5.3	0.2	0.209		
K0	2	2.2	0.079	0.087		
t	0.30 ± 0.05		0.012 ±	0.002		

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